

MICRO ELECTRONICS

**MI38T
MIB38T
(MIB38T-K)
INFRARED
EMITTING
DIODE**

DESCRIPTION

MI38T & MIB38T are GaAlAs infrared emitting diode molded flangeless 3mm diameter clear plastic package, with the lensing effect of the package, and MIB38T with cup type leadframe, MI38T & MIB38T are mechanically and spectrally matched to the MEL82 series photo transistor.

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	160mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10 μ s, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MI38T	MIB38T	UNIT	CONDITIONS
Radiant Power Output	TYP Po	2.0	2.5	mW	IF=20mA
Forward Voltage	MAX VF	1.6	1.6	V	IF=20mA
Reverse Current	MAX IR	100	100	μ A	VR=5V
Half Intensity Beam Angle	TYP θ_{HI}	30	20	degree	IF=20mA
Peak Wavelength	TYP λ_p	940	940	nm	IF=20mA
Spectrum Line Half Width	TYP $\Delta\lambda$	45	45	nm	IF=20mA

Page 1 of 3

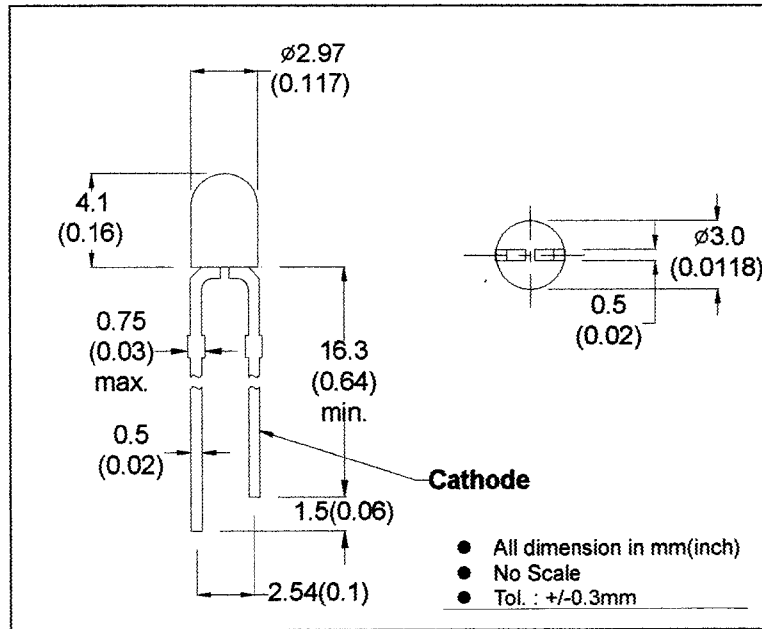
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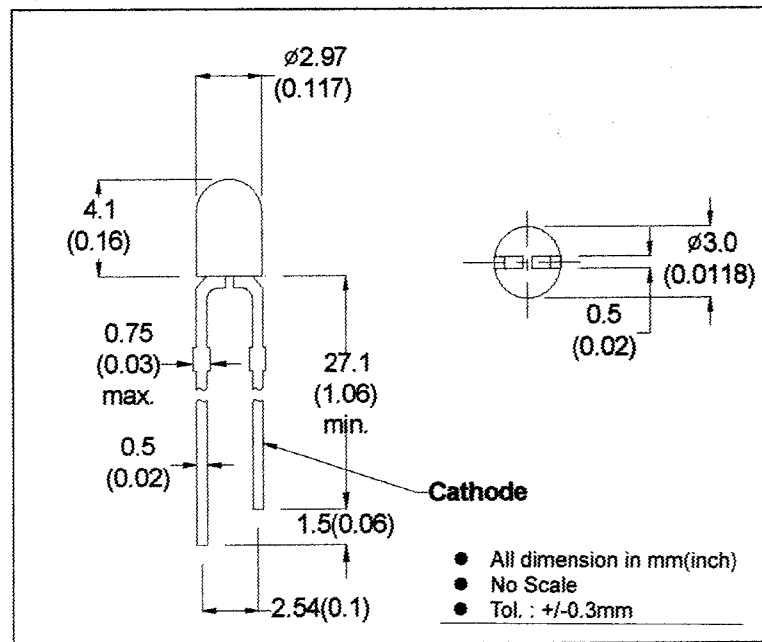
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MECHANICAL OUTLINE

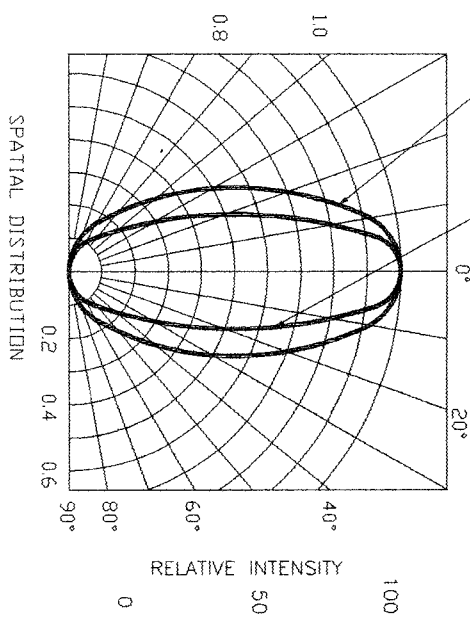
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